

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

MJE2955T PNP
MJE3055T NPN

COMPLEMENTARY SILICON
PLASTIC POWER TRANSISTORS

JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE2955T, MJE3055T are complementary Silicon Plastic Power Transistors designed for high current amplifier and switching applications.

MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	70	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EB0}	5.0	V
Collector Current	I _C	10	A
Base Current	I _B	6.0	A
Power Dissipation	P _D	75	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 TO +150	°C
Thermal Resistance	θ _{JC}	1.67	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CB0}	V _{CB} =70V		1.0	mA
I _{CB0}	V _{CB} =70V, T _C =150°C		10	mA
I _{CEV}	V _{CE} =70V, V _{EB} (OFF)=1.5V		1.0	mA
I _{CEV}	V _{CE} =70V, V _{EB} (OFF)=1.5V, T _C =150°C		5.0	mA
I _{CEO}	V _{CE} =30V		700	μA
I _{EBO}	V _{BE} =5.0V		5.0	mA
h _{FE}	V _{CE} =4.0V, I _C =4.0A	20	100	
h _{FE}	V _{CE} =4.0V, I _C =10A	5.0		
V _{CE} (SAT)	I _C =4.0A, I _B =0.4A		1.1	V
V _{CE} (SAT)	I _C =10A, I _B =3.3A		8.0	V
V _{BE} (ON)	V _{CE} =4.0V, I _C =4.0A		1.8	V
f _T	V _{CE} =10V, I _C =500mA, f=500kHz	2.0		MHz